

Application Number: 09/982,003  
Filing Date: October 19, 2001  
Attorney Docket Number: 04329.2688

**IN THE CLAIMS:**

The proposed amendment to claim 1 is as follows:

1. (Proposed Amendment) A method of manufacturing a semiconductor device comprising:
- preparing a substrate to be treated; and
  - forming an insulation film above the substrate, which includes:
    - applying an insulation film raw material above the substrate, the insulation film raw material including a substance or a precursor of the substance, the insulation film comprising the substance[[,]; **and**
    - curing the insulation film raw material by irradiating an electron beam on the substrate while heating the substrate at a **first** heating temperature **and holding the first heating temperature** <sup>(constant)</sup> in a reactor chamber, and causing to change temperature of the substrate from **[[a]]** **the first heating temperature** to a second heating temperature **different from the first heating temperature and hold the second heating temperature** during the electron beam irradiating process.

*Claims 22 – 25: Change dependency to depend from claim 21.*

30. (New Proposed Claim) The method according to claim 1, wherein the second heating temperature is lower than the first heating temperature.

31. (New Proposed Claim) A method of manufacturing a semiconductor device comprising:

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preparing a substrate to be treated; and  
forming an insulation film above the substrate, which includes:  
applying an insulation film raw material above the substrate, the insulation film raw material including a substance or a precursor of the substance, the insulation film comprising the substance; heating the substrate to a first heating temperature; and  
curing the insulation film raw material by irradiating an electron beam on the substrate while heating the substrate at a second heating temperature different from the first heating temperature in a reactor chamber, and changing temperature of the substrate from the second heating temperature to a third heating temperature different from the second heating temperature and holding the third heating temperature during the electron beam irradiating process.

32. (New Proposed Claim) The method according to claim 31, wherein the third heating temperature is lower than the second heating temperature.

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